

**INFORMATION DISCLOSURE STATEMENT PURSUANT TO**  
**37 C.F.R. §§1.97-1.99**

*PATENT APPLICATION*

Applicant(s): Daniel C. Edelstein *et al.*

Docket No.: END920030116US1

**FOR: HIGH Q FACTOR INTEGRATED CIRCUIT INDUCTOR**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. §1.56 and pursuant to 37 C.F.R. §§1.97-1.99, Applicant(s) hereby notifies the U.S. Patent and Trademark Office of the documents listed on the attached Form PTO-1449. Applicant respectfully submits that all pending claims are patentable over the foregoing references, alone or in combination. The Examiner is requested to initial the enclosed Form PTO-1449 and return a copy thereof to the undersigned.

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicant reserves the right to dispute any of the listed documents as prior art during examination. Further, Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application. Furthermore, the submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other material information may exist. This Information Disclosure Statement is being filed within three months of the filing date of the captioned patent application, and therefore no certification under 37 C.F.R. §1.97(e) or fee under 37 C.F.R. §1.17(p) is required.

Respectfully submitted,

Dated: 12/02/2003

By Jack P. Friedman  
Jack P. Friedman  
Reg. No. 44,688

Enclosures: PTO-1449

<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>	ATTY DOCKET NO. <b>END920030116US1</b>	SERIAL NO.
	<b>Danicel C. Edelstein et al.</b>	
	FILING	GROUP

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	US2002/0172025	11/2002	Megahed et al.			
	US2003/0067052	4/2003	Matsuo et al.			
	US2002/0197844	12/2002	Johnson et al.			
	6,551,931	4/2003	Edelstein et al.			
	6,534,374	3/2003	Johnson et al.			
	6,457,234	10/2002	Edelstein et al.			
	6,444,517	9/2002	Hsu et al.			
	6,368,484	4/2002	Volant et al.			
	6,335,104	1/2002	Sambucetti et al.			
	6,333,559	12/2001	Costrini et al.			
	6,323,128	11/2001	Sambucetti et al.			

**FOREIGN PATENT DOCUMENTS**

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
					YES	NO
WO03017479A2	2/2003	PCT				

**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

		Research Disclosure, April 2000, AN ON-CHIP THREE-DIMENSIONAL INDUCTOR BY DAMASCENE PROCESS, pages 682-683.
		Burghartz et al., MONOLITHIC SPIRAL INDUCTORS FABRICATED USING A VLSI CU-DAMASCENE INTERCONNECT TECHNOLOGY AND LOW-LOSS SUBSTRATES, pages 4.5.1-4.5.4, 1996 IEEE.

EXAMINER	DATE CONSIDERED
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>	ATTY DOCKET NO. <b>END920030116US1</b>	SERIAL NO.
	<b>Danice! C. Edelstein et al.</b>	
	FILING	GROUP

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6,297,140	10/2001	Uzoh et al.			
	6,251,528	6/2001	Uzoh et al.			
	6,187,680	2/2001	Costrini et al.			
	6,133,136	10/2000	Edelstein et al.			
	6,114,937	9/2000	Burghartz et al.			
	6,054,329	4/2000	Burghartz et al.			
	5,884,990	3/1999	Burghartz et al.			
	5,793,272	8/1998	Burghartz et al.			

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DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
					YES	NO

**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

		Edelstein et al., SPIRAL AND SOLENOIDAL INDUCTOR STRUCTURES ON SILICON USING CU-DAMASCENE INTERCONNECTS, 1998 IEEE, pages 18-20.
		Burghartz et al., SPIRAL INDUCTORS AND TRANSMISSION LINES IN SILICON TECHNOLOGY USING COPPER-DAMASCENE INTERCONNECTS AND LOW-LOSS SUBSTRATES, 1997IEEE, pages 1961-1968.

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